



MEMC 98-4650(2293)  
PATENT

#12/3  
10/23/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Gregory Michael Wilson et al.  
Serial No. 09/608,302  
Filed June 30, 2000  
Confirmation No. 9819  
For A METHOD AND APPARATUS FOR FORMING A SILICON WAFER WITH A  
DENUDED ZONE  
Examiner Robert M. Kunemund

Art Unit 1765

October 17, 2002

AMENDMENT B

RECEIVED  
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TO THE ASSISTANT COMMISSIONER FOR PATENTS,

SIR:

In response to the Office action of dated May 17, 2002, please enter the following amendments:

IN THE CLAIMS:

Please replace claim 1 with the following:

1. (twice amended) A method of producing a template for oxygen precipitation in a semiconductor wafer in a housing having a source of heat, a susceptor, a wafer support and a Bernoulli wand, said method including:

heating a semiconductor wafer with opposite major surfaces in the housing to an elevated temperature of at least about 1175°C with a heat source, said semiconductor being supported by the support in the housing during said heating;

ceasing said heating and moving said semiconductor out of conductive heat transfer relation with the support with the Bernoulli wand; and

cooling said heated wafer in the housing while holding said wafer out of conductive heat transfer relationship with the support at a rate of at least 10°C/sec until the wafer reaches a temperature of less than about 850°C thereby forming a template for oxygen precipitation in the wafer.

Please replace claim 2 with the following:

2. (twice amended) A method as set forth in claim 1 wherein the process additionally comprises the step of placing the wafer in the housing and applying an epitaxial coating to at least one said major surface thereof before said heating step with said wafer being in immediate heat transfer relation with the support during at least a portion of the coating application.